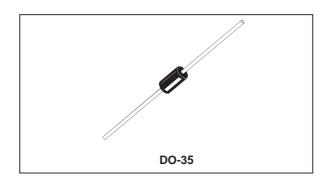


SMALL SIGNAL SCHOTTKY DIODE

DESCRIPTION

Metal to silicon junction diode featuring high breakdown, low turn-on voltage and ultrafast switching. Primarly intended for high level UHF/VHF detection and pulse application with broad dynamic range. Matched batches are available on request



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit	
V_{RRM}	Repetitive Peak Reverse Voltage		70	V
l _F	Forward Continuous Current*	15	mA	
P _{tot}	Power Dissipation*	430	mW	
$T_{stg} \\ T_{j}$	Storage and Junction Temperature Range	- 65 to 200 - 65 to 200	°C	
TL	Maximum Lead Temperature for Soldering dur from Case	230	°C	

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R _{th(j-a)}	Junction-ambient*	400	°C/W

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions	Min.	Тур.	Max.	Unit
V_{BR}	$T_{amb} = 25$ °C $I_R = 10\mu A$	70			V
V _F * *	$T_{amb} = 25^{\circ}C$ $I_F = 1mA$			0.41	V
	$T_{amb} = 25$ °C $I_F = 15$ mA			1	
I _R * *	$T_{amb} = 25$ °C $V_R = 50V$			0.2	μА

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Тур.	Max.	Unit
С	T _{amb} = 25°C	$V_R = 0V$	f = 1MHz			2	pF
τ	T _{amb} = 25°C	$I_F = 5mA$	Krakauer Method			100	ps

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^{*} On infinite heatsink with 4mm lead length
** Pulse test: $t_p \le 300 \mu s \delta < 2\%$.
Matched batches available on request. Test conditions (forward voltage and/or capacitance) according to customer specification.

Fig. 1: Forward current versus forward voltage at low level (typical values).

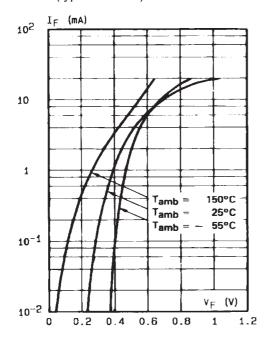


Fig. 2: Capacitance C versus reverse applied voltage $V_{\scriptscriptstyle R}$ (typical values).

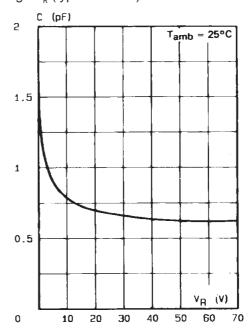


Fig. 3: Reverse current versus ambient temperature.

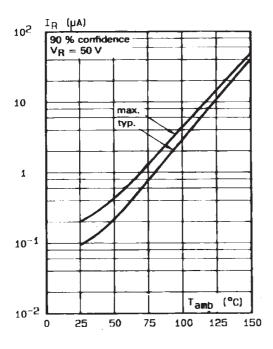
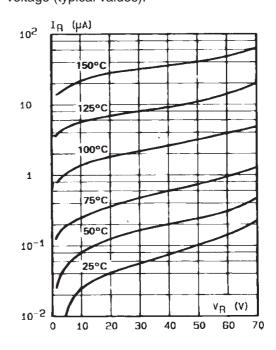


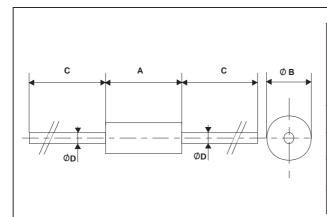
Fig. 4: Reverse current versus continuous reverse voltage (typical values).



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PACKAGE MECHANICAL DATA

DO-35



REF.	DIMENSIONS			
	Millimeters		Inc	hes
	Min.	Max.	Min.	Max.
А	3.05	4.50	0.120	0.177
В	1.53	2.00	0.060	0.079
С	28.00		1.102	
D	0.458	0.558	0.018	0.022

Cooling method: by convection and conduction Marking: clear, ring at cathode end. Weight: 0.15g

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